

2SB15040QA Datasheet

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DiGi Electronics Part Number 2SB15040QA-DG

Manufacturer Panasonic Electronic Components

Manufacturer Product Number 2SB15040QA

Description TRANS PNP DARL 50V 8A MT-3

Detailed Description Bipolar (BJT) Transistor PNP - Darlington 50 V 8 A 2

0MHz 1.5 W Through Hole MT-3-A1



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.



Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
2SB15040QA	Panasonic Electronic Components
Series:	Product Status:
-	Obsolete
Transistor Type:	Current - Collector (Ic) (Max):
PNP - Darlington	8 A
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, lc:
50 V	1.5V @ 8mA, 4A
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ lc, Vce:
100μA (ICBO)	2000 @ 4A, 3V
Power - Max:	Frequency - Transition:
1.5 W	20MHz
Operating Temperature:	Mounting Type:
150°C (TJ)	Through Hole
Package / Case:	Supplier Device Package:
3-SIP	MT-3-A1
Base Product Number:	
2SB1504	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):	
RoHS non-compliant	1 (Unlimited)	
ECCN:	HTSUS:	
EAR99	8541.29.0095	

2SB1504

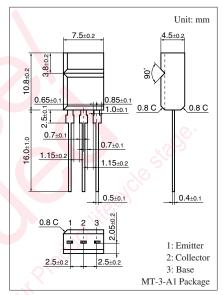
Silicon PNP epitaxial planar type darlington

For power switching

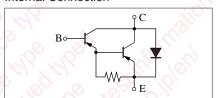
- High forward current transfer ratio hFE
- High-speed switching
- Allowing automatic insertion with radial taping

■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V _{CBO}	-50	V	
Collector-emitter voltage (Base open)	V _{CEO}	-50	V	
Emitter-base voltage (Collector open)	V_{EBO}	-7	V	
Collector current	I_{C}	-8	A	
Peak collector current	I_{CP}	-12	A	
Collector power dissipation	P _C	1.5	W	
Junction temperature	T_{j}	150	°C	
Storage temperature	T_{stg}	-55 to +150	°C	



Internal Connection



■ Electrical Characteristics T_a = 25°C ± 3°C

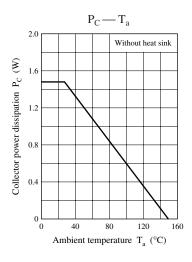
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V _{CEO}	$I_C = -30 \text{ mA}, I_B = 0$	-50	250		V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -50 \text{ V}, I_E = 0$	-W		-100	μΑ
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = -7 \text{ V}, I_C = 0$	7.9		-2	mA
Forward current transfer ratio	h _{FE1} *	$V_{CE} = -3 \text{ V}, I_{C} = -4 \text{ A}$	1 000		10 000	_
	h _{FE2}	$V_{CE} = -3 \text{ V}, I_{C} = -8 \text{ A}$	500			
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = -4 \text{ A}, I_B = -8 \text{ mA}$			-1.5	V
Base-emitter saturation voltage	V _{BE(sat)}	$I_C = -4 \text{ A}, I_B = -8 \text{ mA}$			-2.0	V
Transition frequency	f_T	$V_{CB} = -10 \text{ V}, I_E = 0.5 \text{ A}, f = 200 \text{ MHz}$		20		MHz
Turn-on time	t _{on}	$I_C = -4 \text{ A}, I_{B1} = -8 \text{ mA}, I_{B2} = 8 \text{ mA}$		0.5		μs
Storage time	t _{stg}	$V_{CC} = -50 \text{ V}$		2.0		μs
Fall time	t _f			1.0		μs

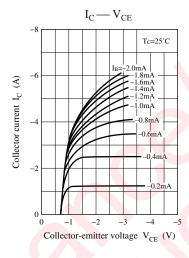
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

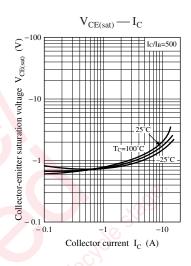
2. *: Rank classification

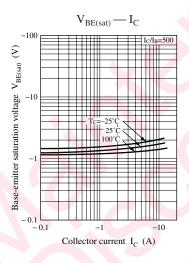
Rank	Р	Q	R
h _{FE1}	1000 to 2500	2000 to 5000	4000 to 10000

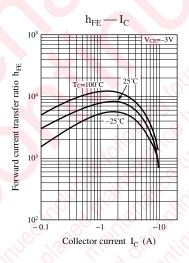
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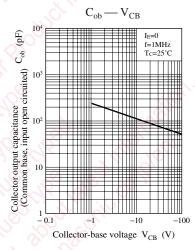


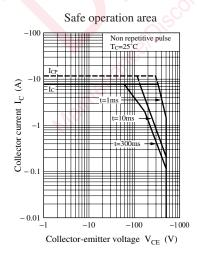


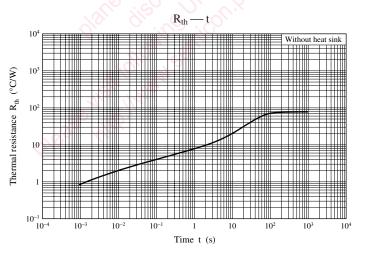












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